

TECHNICAL DATA DATA SHEET 877, REV. C

SILICON ULTRA-FAST RECOVERY EPITAXIAL RECTIFIER DIE

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

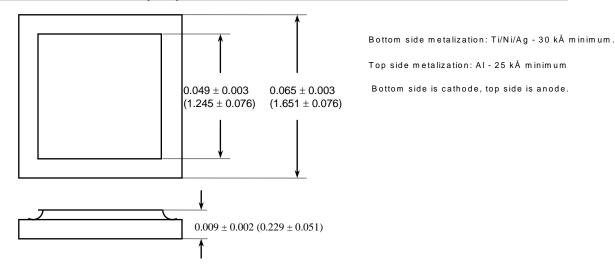
- Glass Passivated Epitaxial Diode with Mesa Structure
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop and Low Reverse Current
- Electrically and Mechanically Stable during and after Packaging

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^{\circ}$ C unless otherwise specified.

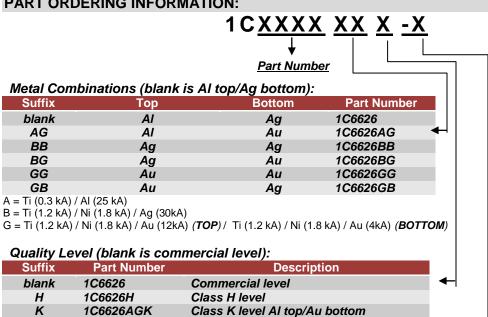
Rating	Symbol	Condition	Max	Units
WORKING PEAK REVERSE VOLTAGE 1C6626 1C6627 1C6628 1C6629 1C6630 1C6631	Vrwm		200 400 600 800 900 1000	Volts
AVERAGE RECTIFIED FORWARD CURRENT 1C6626 thru 1C6628 1C6629 thru 1C6631	Io	T _A = 75 °C	2.3 1.8	Amps
PEAK FORWARD SURGE CURRENT 1C6626 thru 1C6630 1C6631	I _{FSM}	T _p =8.3ms	75 60	A(pk)
MAXIMUM REVERSE CURRENT 1C6626 thru 1C6630 1C6631	I _R @ V _{RWM}	T _j = 25 °C	2.0 4.0	μAmps
MAXIMUM REVERSE CURRENT 1C6626 thru 1C6630 1C6631	I _R @ V _{RWM}	T _j = 150 °C	500 600	μAmps
MAX. PEAK FORWARD VOLTAGE (PULSED) 1C6626 thru 1C6628 1C6629 to 1C6630 1C6631	V _{FM}	I _F =4A I _F =3A I _F =2A	1.50 1.70 1.95	Volts
MAXIMUM REVERSE RECOVERY TIME 1C6626 thru 1C6628 1C6629 to 1C6630 1C6631	T _{rr}	I _F =0.5A I _{RM} =1.0A	30 50 60	ns

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Dimensions in inches (mm):



PART ORDERING INFORMATION:



Polarity (blank is anode top/cathode bottom):

Suffix	Тор	Bottom	Part Number
blank	Anode	Cathode	1C6626
-R	Cathode	Anode	1C6626AGK-R

SENSITRON SEMICONDUCTOR

1C6626 thru 1C6631

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